

Amendments to the Specification

Please replace the paragraph beginning on page 7, line 13 with the following amended paragraph:

The device of Figure 2 uses a design similar to that of Figures 1a and 1b, except for depositing the electrode 12 into the hollowed out area 27 on the insulating film 28 (e.g., SiO₂, Si₃N₄, MgO) and covering the electrode with such insulating dielectric as well. One may note that in both devices 10 and 20, electrodes 11, 12, 13, 14, and thus the leads to them, may be located on two wafers 15 and 16. Electrodes 11 and 12 may be on the bottom wafer 15. Electrodes 13 and 14 may be attached to the top wafer. In both devices 10 and 20, the top wafer 16 may form the gas flow channel 17, for the sample gas flow 29, of the separation column, and the bottom wafer 15, in the situation of PHASED sensors, may support the column heaters. The gas flow 29 may flow through a separator, filter, spectrometer, and/or processor 70.